

**Silicon Carbide Schottky Diode**

V_{RRM}	1200V
I_F 135°C	28A
Q_C	

Features

Positive temperature coefficient
 Temperature-independent switching
 Maximum working temperature at 175 °C
 Unipolar devices and zero reverse recovery current
 Zero forward recovery current
 Essentially no switching losses
 Reduction of heat sink requirements
 High-frequency operation
 Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-220AC

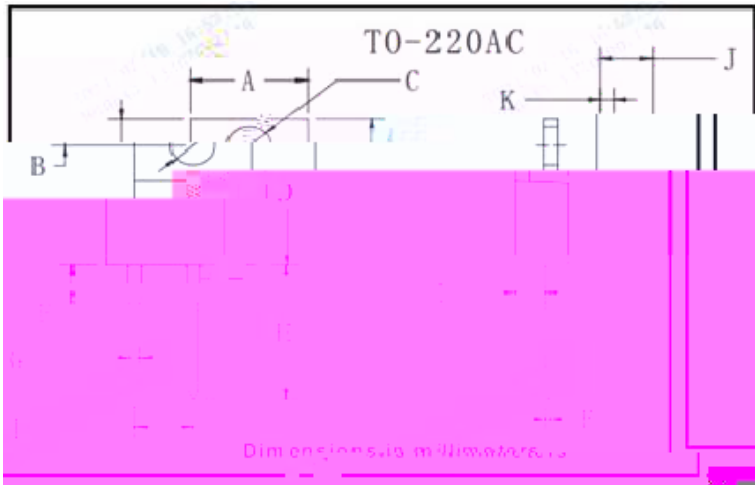
Terminals: Tin plated leads

Polarity: As marked

Maximum Ratings ($T_c=25$)

			J 5 @ I 9
Device marking code			D112020PGG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	1200
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	1200
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	61
Continuous forward current @ $T_c=135^\circ\text{C}$			28
Continuous forward current @ $T_c=150^\circ\text{C}$			20
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	160
Power Dissipation @ $T_c=25^\circ\text{C}$	P_{TOT}	W	241
Power Dissipation @ $T_c=110^\circ\text{C}$			104
i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	i^2t	A^2S	128
Operating junction and Storage temperature range	T_j, T		

Outline Dimensions



TO-220AC		
Dim	Min	Max
A	9.95	10.35
B	2.55	2.95
C	3.75	4.05
D	14.95	15.25
E	3.75	4.25
F	0.26	0.5
G	0.68	0.94
H	13.3	13.9
I	4.86	5.26
J	4.38	4.78
K	1.14	1.4
L	2.37	2.79



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